XP01112

Silicon PNP epitaxial planar type

For digital circuits

- Features
- Two elements incorporated into one package (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

Basic Part Number

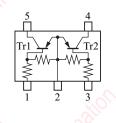
• UNR1112 × 2

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-50	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Collector current	I _C	-100	mA	
Total power dissipation	P _T	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



- 1: Base (Tr1)4: Collector (Tr2)2: Emitter5: Collector (Tr1)
- 3: Base (Tr2)
- Marking Symbol: 7K
- Internal Connection



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

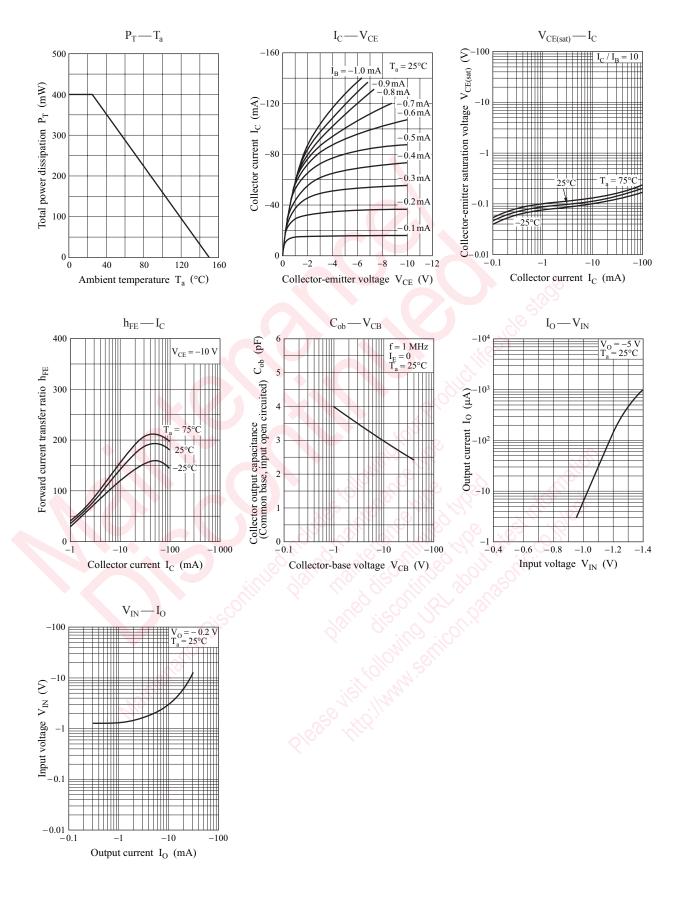
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu {\rm A}, I_{\rm E} = 0$	-50	0, 3	8	V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$		2.	- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$	And Co		- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = -6 V, I_C = 0$	Х,		- 0.2	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	60			
h _{FE} ratio *	h _{FE (Small/} Large)	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.5	0.99		_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V _{OH}	$V_{\rm CC} = -5 \text{ V}, V_{\rm B} = -0.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V _{OL}	$V_{CC} = -5 V, V_B = -2.5 V, R_L = 1 k\Omega$			- 0.2	V
Input resistance	R ₁		-30%	2.2	+30%	kΩ
Resistance ratio	R ₁ / R ₂		0.8	1.0	1.2	
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. * : Ratio between 2 elements

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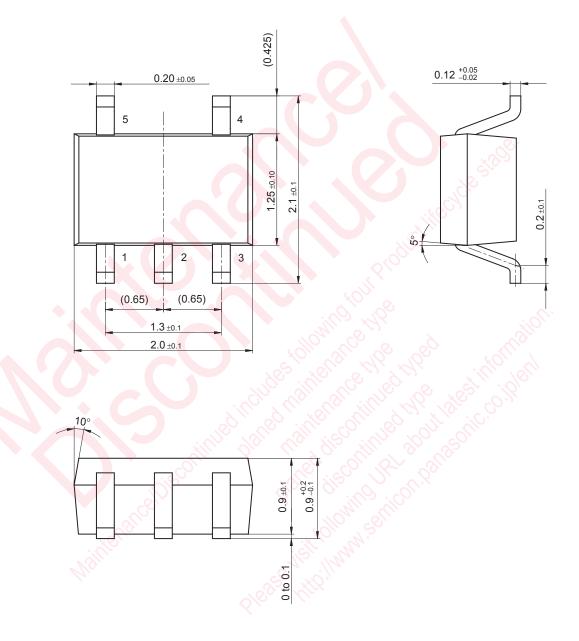
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SMini5-G1

Unit: mm



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